

FORM PTO 1449 (modified)

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICELIST OF REFERENCES CITED BY APPLICANT(S)
(Use several sheets if necessary)Date Submitted to PTO: **October 20, 2003**ATTY DOCKET NO. **BHT/3230-56**APPLICATION NO. **10/601,701**APPLICANT **YEH**FILING DATE **Jun 24, 2003**GROUP **2812**

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
SDI	4,330,363	05/18/82	Blegesen et al.			
	4,592,799	06/03/86	Hayafuji			
	5,021,119	06/04/91	Fan et al.			
	5,395,481	03/07/95	McCarthy			
	6,495,405 B2	12/17/02	Voutsas et al.			

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT

OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)

SDI	High-Performance Low-Temperature Poly-Si TFTs Crystallized by Excimer Laser with Recessed-Channel Structure, Lin et al., IEEE Electron Device Letters, Vol. 22, No. 6, June 2001, pages 269-271
↑	Performance Improvement Obtained for Thin-Fil Transistors Fabricated in Prepatterned Laser-Recrystallized Polysilicon, Giust et al., IEEE Electron Device Letters, Vol. 18, No. 6, June 1997, pages 296-298
	Comparison of excimer laser recrystallized prepatterned and unpatterned silicon films on SiO₂, Giust et al., J.Appl.Phys. 81(3), 1 February 1997, pages 1204-1211
	High-Performance Single Crystalline-Silicon TFTs on a Non-Alkali Glass Substrate, Sano et al. Fujitsu Laboratories Ltd., Atsugi 243-0197, Japan (C) 2002 IEEE

EXAMINER

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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.